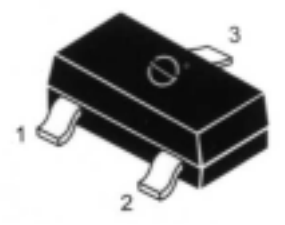
Shandong Yiguang Electronic Joint stock Co., Ltd

SEMICONDUCTOR
TECHNICAL DATA

2SA1015LT1

PNP EPITAXIAL SILICON TRANSISTOR

Package:SOT-23



PIN: / STYLE	1	2	3
NO.1	B	E	C

* Complement to 2SC1815

* Collector Current : Ic=150mA

ABSOLUTE MAXIMUM RATINGS at Ta=25℃

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	-60	V
Collector-Emitter Voltage	Vceo	-50	V
Emitter-Base Voltage	Vebo	-5	V
Collector Current	Ic	-150	mA
Collector Dissipation Ta=25℃*	P_D	225	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55-150	℃

ELECTRICAL CHARACTERISTICS at Ta=25℃

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	-60			V	Ic= -100uA Ie=0
Collector-Emitter Breakdown Voltage#	BVceo	-50			V	Ic= -1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	-5.0			V	Ie= -100uA Ic=0
Collector-Base Cutoff Current	Icbo			-100	nA	Vcb= -50V Ie=0
Emitter-Base Cutoff Current	Iebo			-100	nA	Veb= -3V Ic= 0
DC Current Gain	Hfe	70		700		Vce= -6V Ic= -2mA
Collector-Emitter Saturation Voltage	Vce(sat)			-0.30	V	Ic= -100mA Ib= -10mA

* Total Device Dissipation : FR=1X0.75X0.062in Board,Derate 25℃.

\# Pulse Test : Pulse Width ≤300uS,Duty cycle ≤2%

DEVICE MARKING:

2SA1015=M6

Fig.1 Grounded emitter propagation characteristics

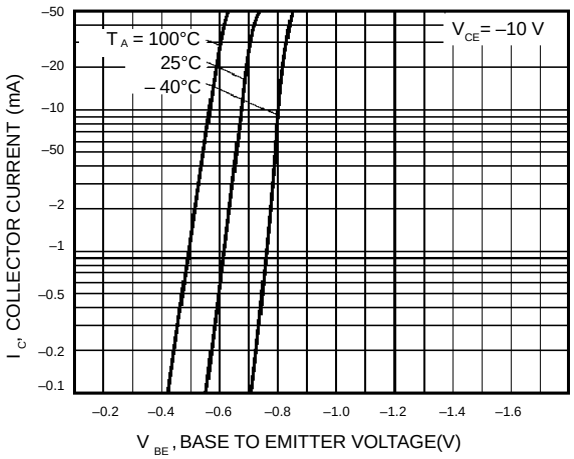


Fig.2 Grounded emitter output characteristics(Ⅰ)

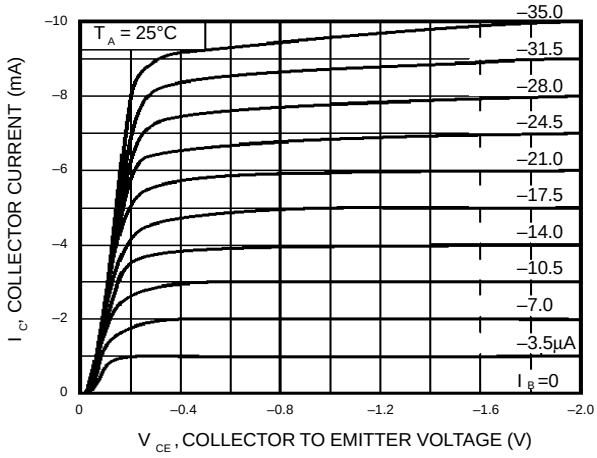


Fig.3 Grounded emitter output characteristics(Ⅱ)

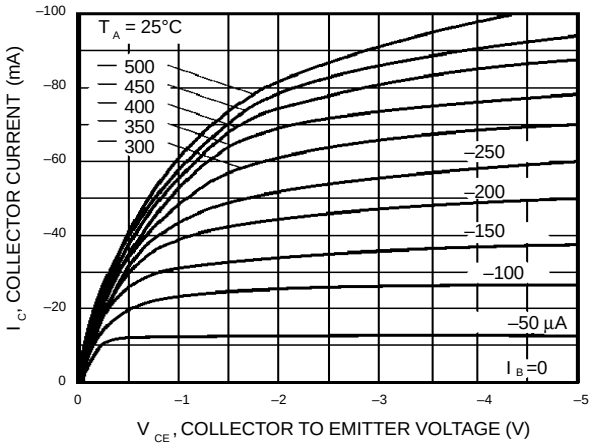


Fig.4 DC current gain vs. collector current (Ⅰ)

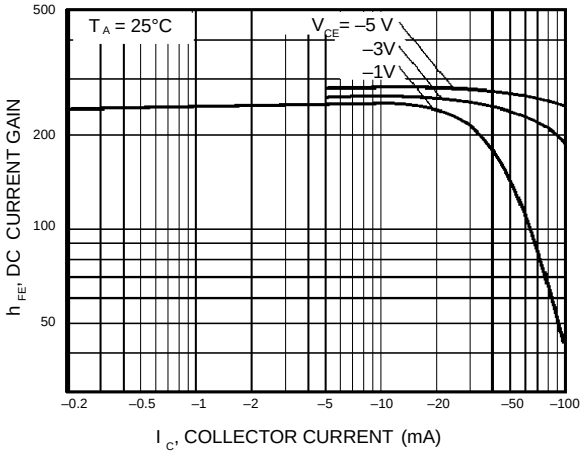


Fig.5 DC current gain vs. collector current (Ⅱ)

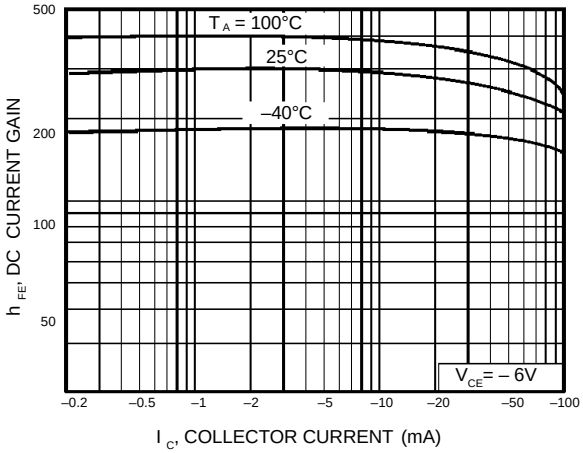


Fig.6 Collector-emitter saturation voltage vs. collector current (Ⅰ)

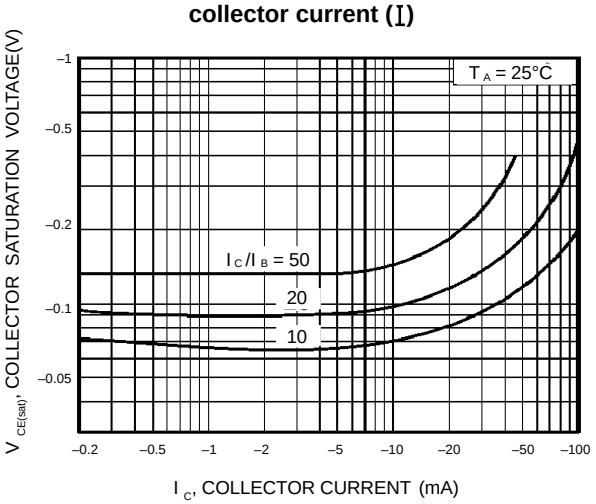


Fig.7 Collector-emitter saturation voltage vs. collector current (Ⅱ)

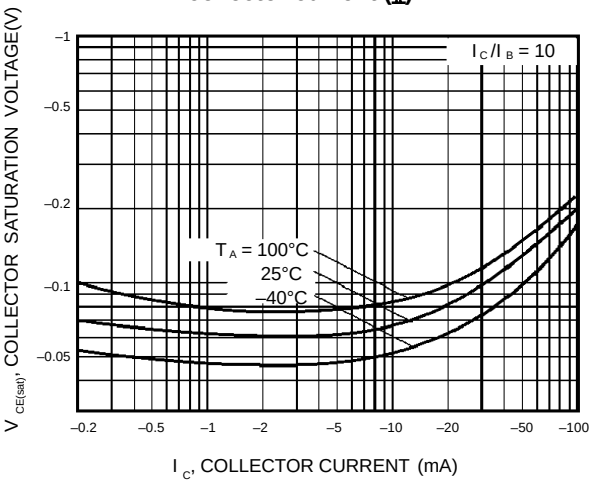


Fig.8 Gain bandwidth product vs. emitter current

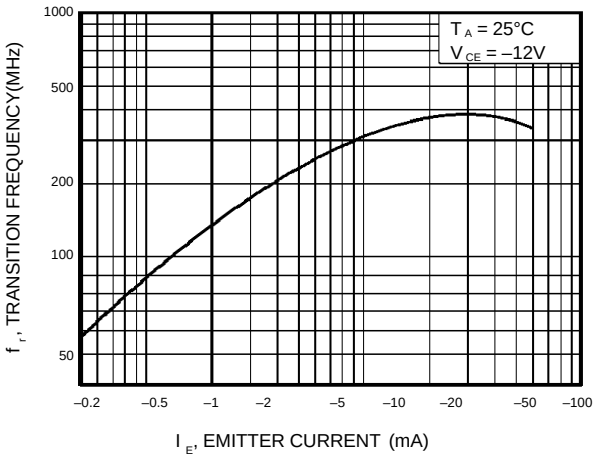


Fig.9 Collector output capacitance vs.collector-base voltage
Emitter inputcapacitance vs. emitter-base voltage